



**TO-126C Plastic-Encapsulate Transistors**

**2SD669**

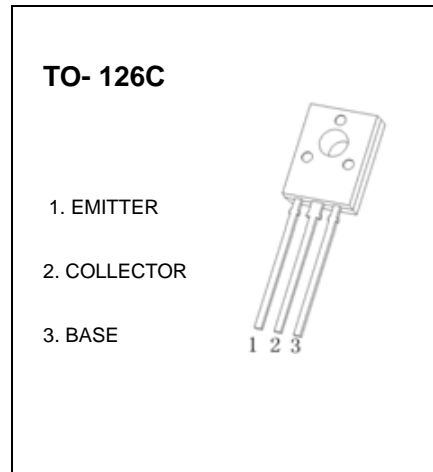
**2SD669A** TRANSISTOR (NPN)

**FEATURES**

- Low Frequency Power Amplifier Complementary Pair with 2SB649/A

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector- Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	2SD669	120
		2SD669A	160
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1.5	A
P <sub>C</sub>	Collector Dissipation	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =1mA, I <sub>E</sub> =0	180			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	2SD669	120		V
			2SD669A	160		
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =160V, I <sub>E</sub> =0			10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			10	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA	2SD669	60	320	
			2SD669A	60	200	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA			1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA		140		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		14		pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank		B	C	D
Range	2SD669	60-120	100-200	160-320
	2SD669A	60-120	100-200	